

N-Channel Power MOSFET

600V, 4A, 0.98Ω

FEATURES

- Super-Junction technology
- High performance due to small figure-of-merit
- High commutation performance
- 100% UIS & R_g tested
- RoHS Compliant
- Halogen-free

KEY PERFORMANCE PARAMETERS

PARAMETER	VALUE	UNIT
V _{DS}	600	V
R _{DS(on)} (max)	0.98	Ω
Q _g	11	nC

APPLICATIONS

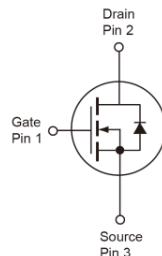
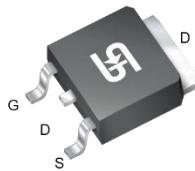
- Switching Power Supply
- Lighting



RoHS
COMPLIANT

**HALOGEN
FREE**

TO-252 (D-PAK)



Note: MSL 3 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DS}	600	V
Gate-Source Voltage	static	±20	V
	AC(f>1Hz)	±30	V
Continuous Drain Current	I _D	4	A
Pulsed Drain Current ^(Note 1)	I _{DM}	12	A
Total Power Dissipation @ T _C = 25°C	P _D	57	W
Single Pulse Avalanche Energy ^(Note 2)	E _{AS}	78	mJ
Single Pulse Avalanche Current ^(Note 2)	I _{AS}	1.8	A
Operating Junction and Storage Temperature Range	T _J , T _{STG}	- 55 to +150	°C

THERMAL PERFORMANCE

PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	R _{θJC}	2.2	°C/W
Junction to Ambient Thermal Resistance	R _{θJA}	50	°C/W

Note: R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. The R_{θJA} limit presented here is based on mounting on a 1 in² pad of 2 oz copper.

ELECTRICAL SPECIFICATIONS ($T_A = 25^\circ\text{C}$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 3)						
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}$, $I_D = 1\text{mA}$	BV_{DSS}	600	--	--	V
Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 1\text{mA}$	$V_{GS(\text{TH})}$	3	4.5	5	V
Gate Body Leakage	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$	I_{GSS}	--	--	± 100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 600\text{V}$, $V_{GS} = 0\text{V}$	I_{DSS}	--	--	100	μA
Drain-Source On-State Resistance	$V_{GS} = 10\text{V}$, $I_D = 1.5\text{A}$	$R_{DS(\text{on})}$	--	0.87	0.98	Ω
Dynamic (Note 4)						
Total Gate Charge	$V_{DS} = 300\text{V}$, $I_D = 4\text{A}$, $V_{GS} = 10\text{V}$	Q_g	--	11	--	nC
Gate-Source Charge		Q_{gs}	--	2.9	--	
Gate-Drain Charge		Q_{gd}	--	4.7	--	
Input Capacitance	$V_{DS} = 300\text{V}$, $V_{GS} = 0\text{V}$, $f = 1.0\text{MHz}$	C_{iss}	--	330	--	pF
Output Capacitance		C_{oss}	--	16	--	
Reverse Transfer Capacitance		C_{rss}	--	11	--	
Gate Resistance	$f = 1.0\text{MHz}$	R_g	--	3	--	Ω
Switching (Note 5)						
Turn-On Delay Time	$V_{DD} = 300\text{V}$, $R_G = 10\Omega$, $I_D = 2\text{A}$, $V_{GS} = 10\text{V}$	$t_{d(on)}$	--	12	--	ns
Turn-On Rise Time		t_r	--	11	--	
Turn-Off Delay Time		$t_{d(off)}$	--	28	--	
Turn-Off Fall Time		t_f	--	17	--	
Source-Drain Diode						
Body-Diode Continuous Forward Current		I_s	--	--	4	A
Body-Diode Pulsed Current (Note 1)		I_{SM}	--	--	12	A
Forward Voltage (Note 3)	$I_s = 1.5\text{A}$, $V_{GS} = 0\text{V}$	V_{SD}	--	--	1.5	V
Reverse Recovery Time (Note 4)	$I_s = 4\text{A}$ $dI_F/dt = 100\text{A}/\mu\text{s}$	t_{rr}	--	237	--	ns
Reverse Recovery Charge (Note 4)		Q_{rr}	--	2.1	--	μC

Notes:

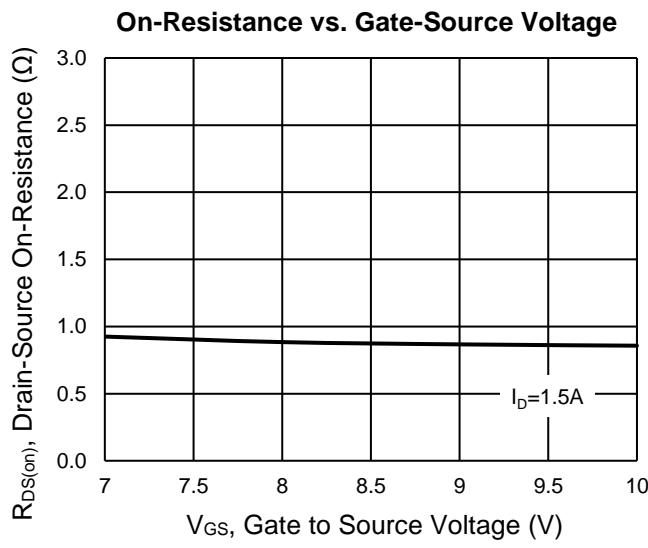
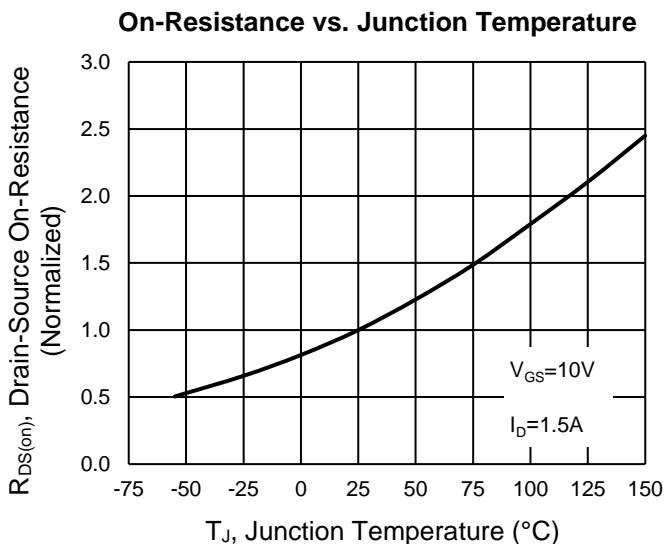
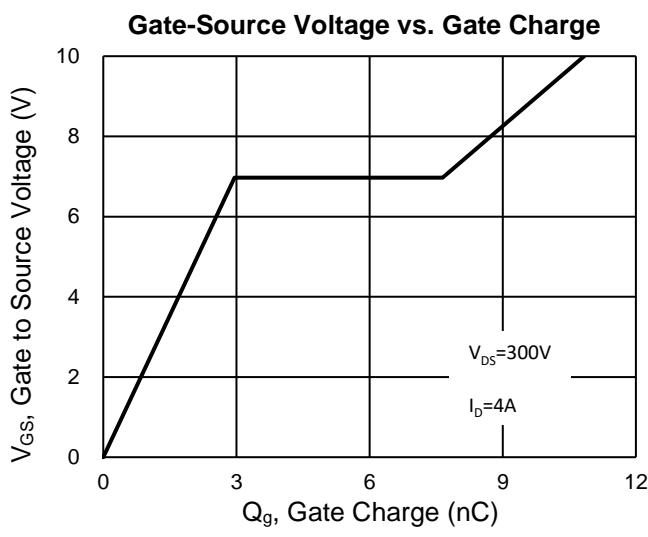
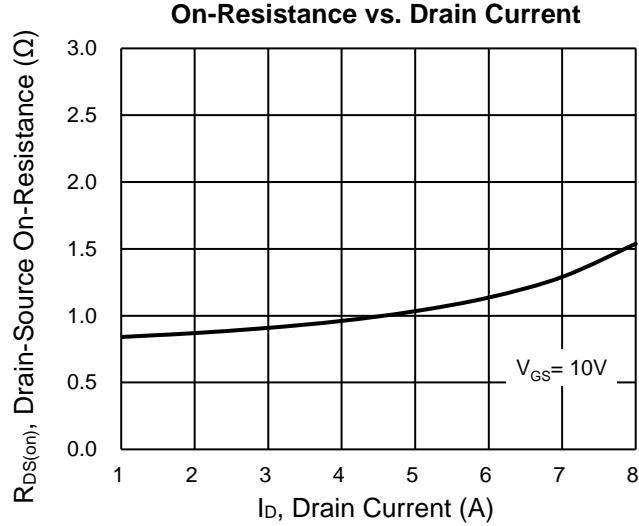
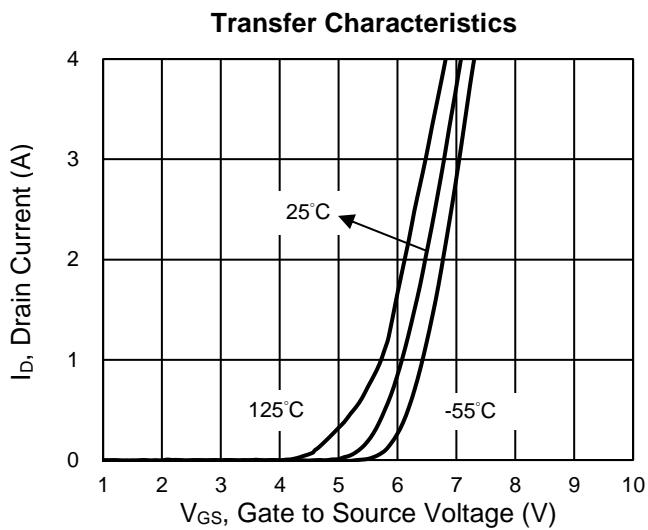
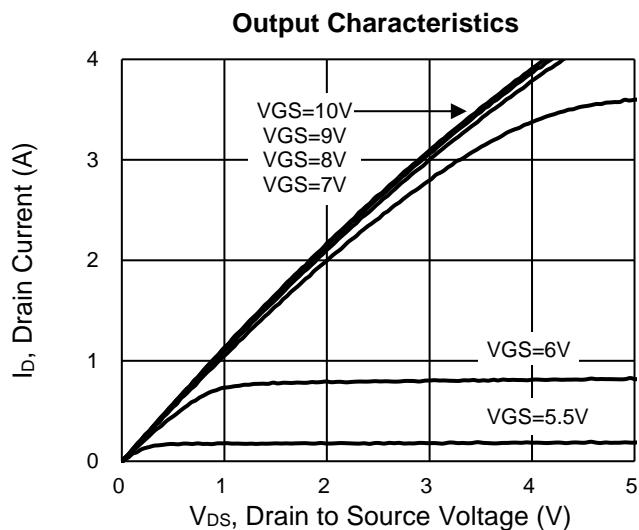
1. Pulse width limited by the maximum junction temperature.
2. $L = 50\text{mH}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. Pulse test: $PW \leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
4. Defined by design. Not subject to production test.
5. Switching time is essentially independent of operating temperature.

ORDERING INFORMATION

ORDERING CODE	PACKAGE	PACKING
TSM60NC980CP ROG	TO-252 (DPAK)	2500pcs / 13" Reel

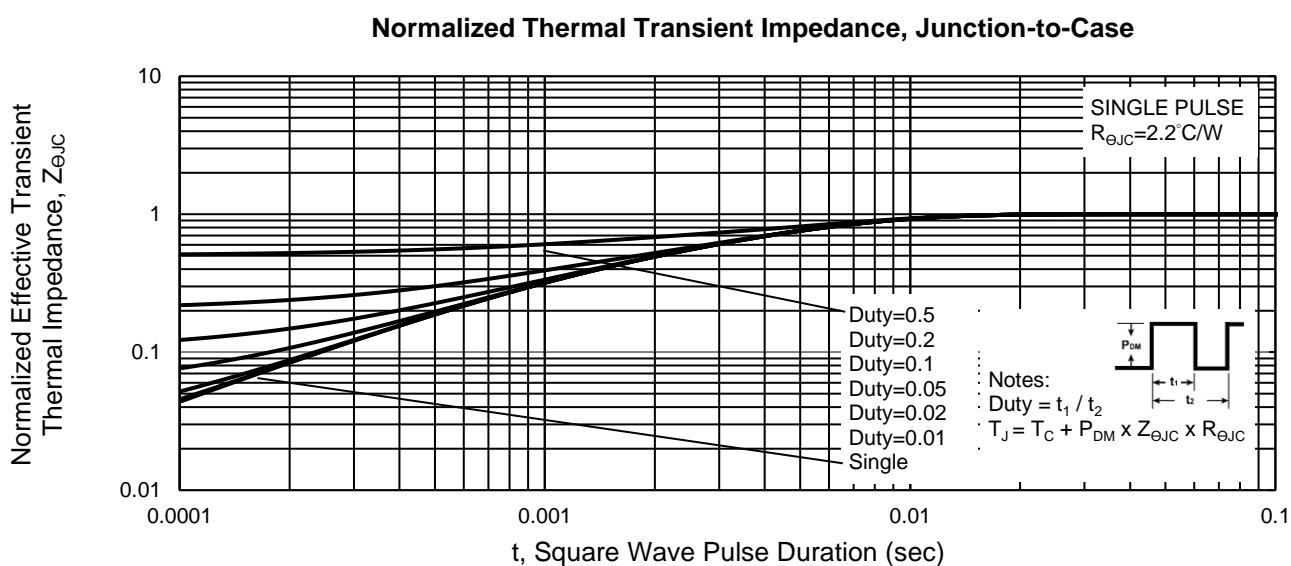
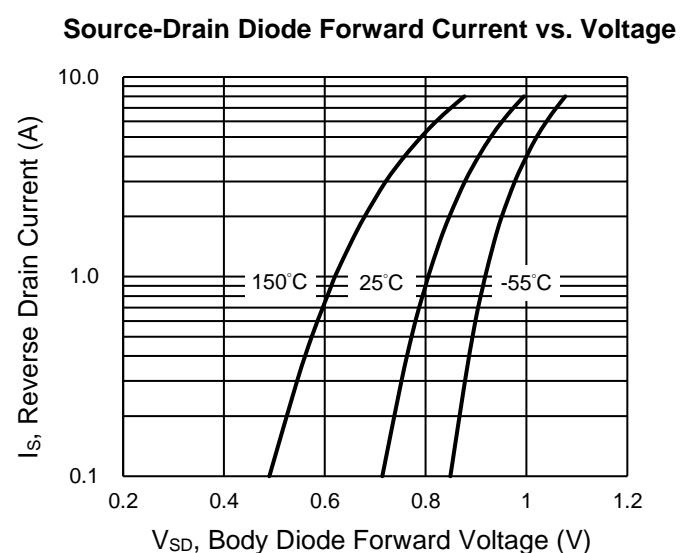
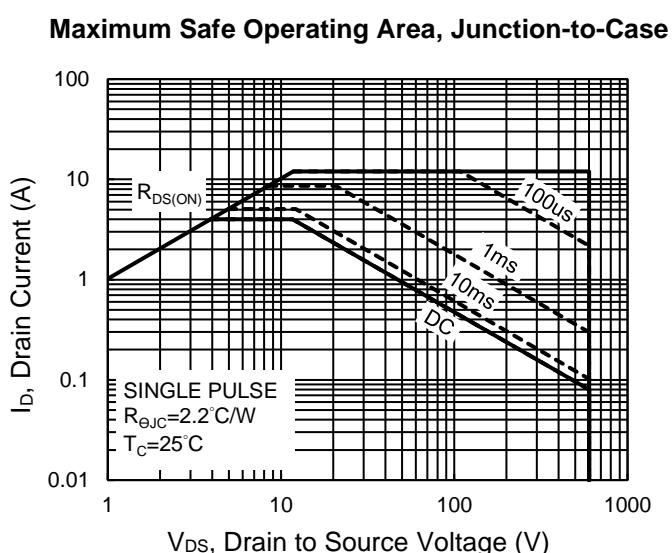
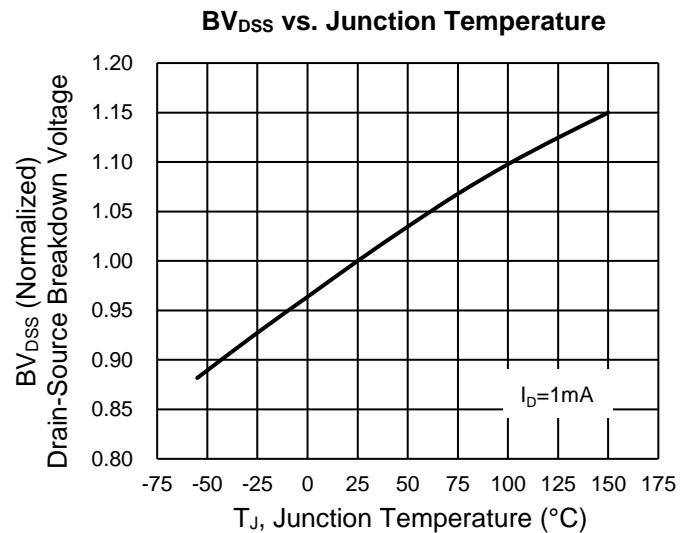
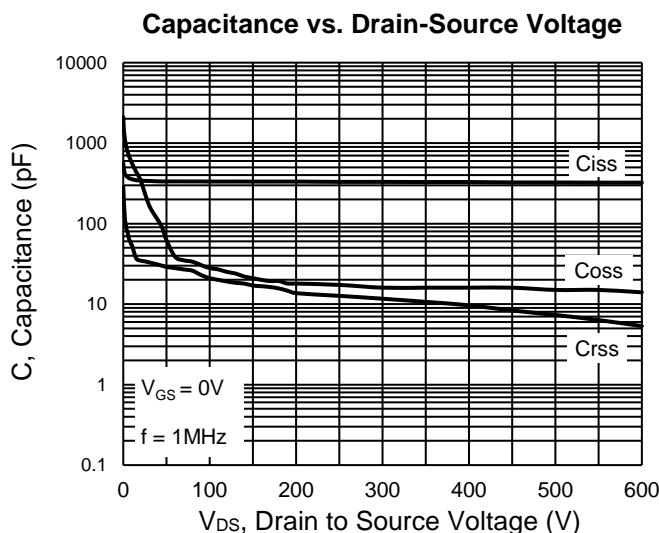
CHARACTERISTICS CURVES

($T_c = 25^\circ\text{C}$ unless otherwise noted)



CHARACTERISTICS CURVES

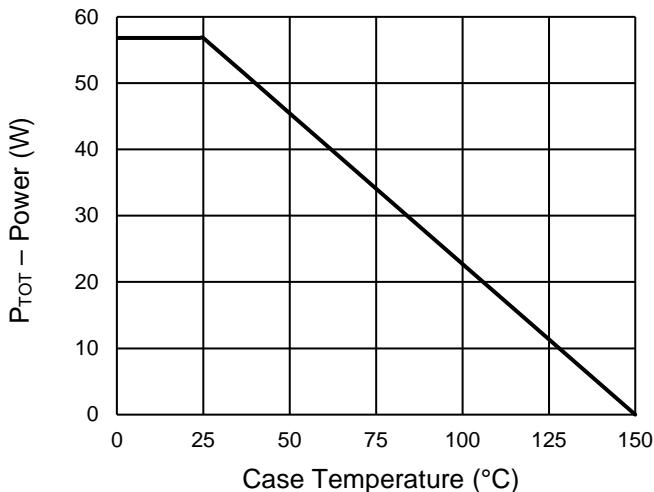
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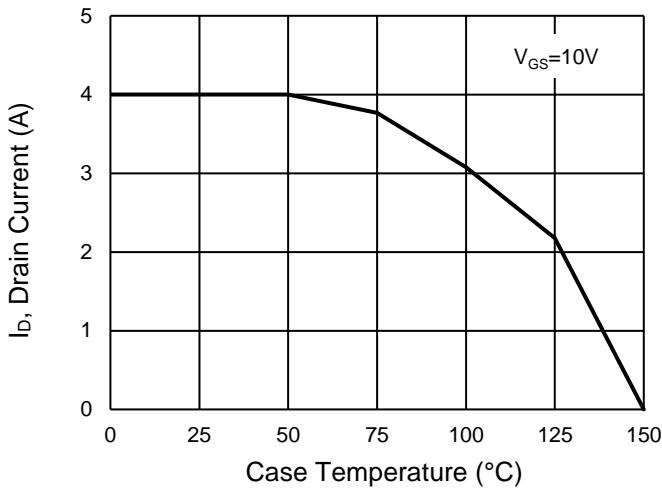
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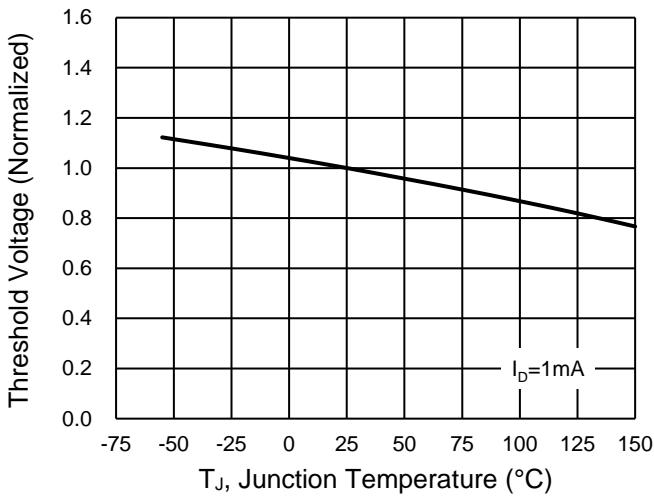
Power Dissipation



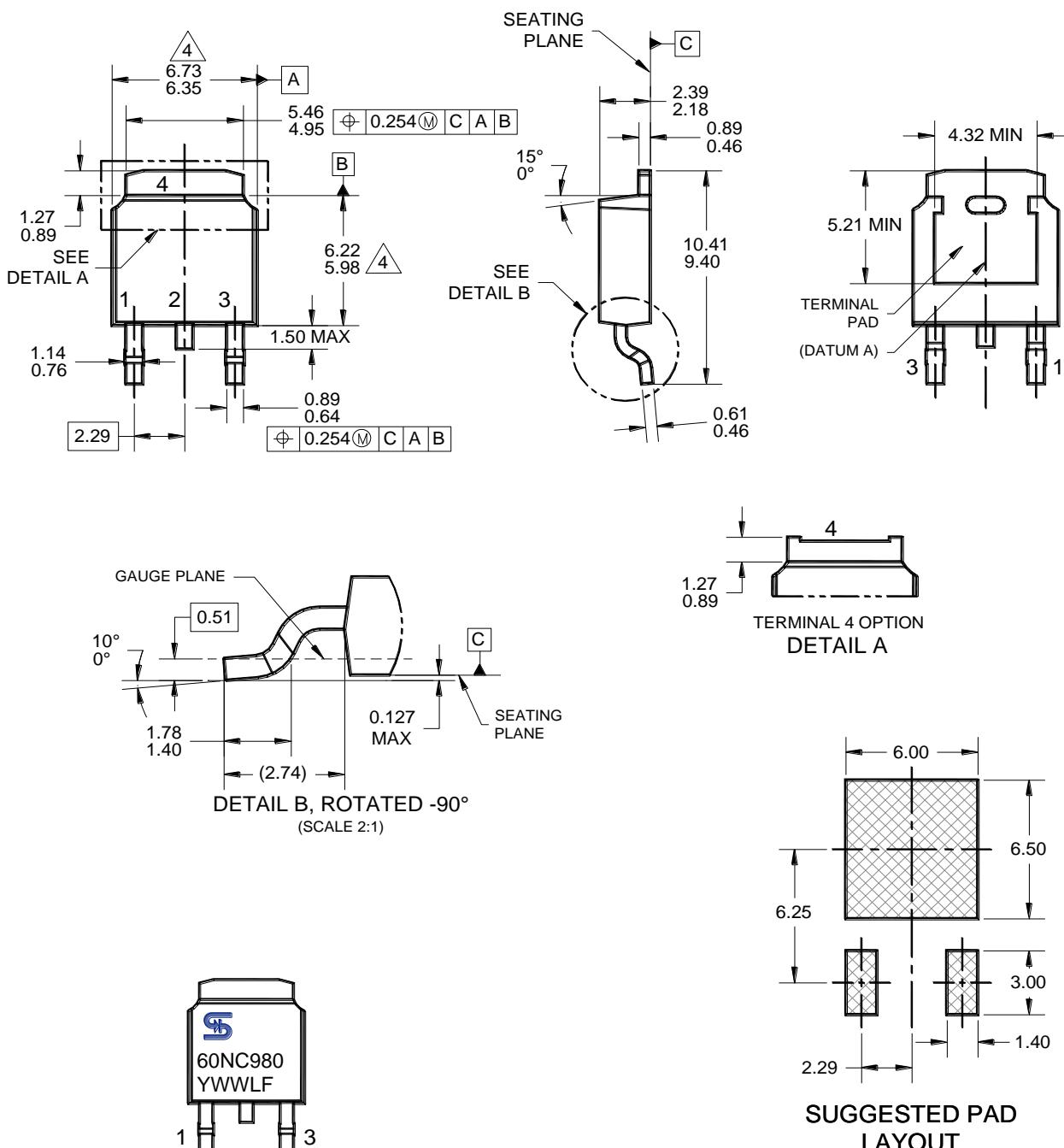
Drain Current



Normalized gate threshold voltage vs Temperature



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

TO-252

MARKING DIAGRAM

Y	= YEAR CODE
WW	= WEEK CODE (01 ~ 52)
L	= LOT CODE (1~9, A~Z)
F	= FACTORY CODE

NOTES: UNLESS OTHERWISE SPECIFIED

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
3. PACKAGE OUTLINE REFERENCE: JEDEC TO-252, VARIATION AA, ISSUE F.
4. MOLDED PLASTIC BODY DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSION, OR GATE BURRS.
5. DWG NO. REF: HQ2SD07-TO252AA-013 REV A.

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